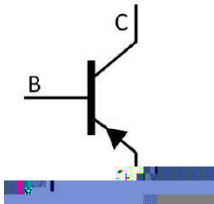


TO-92 PNP Silicon PNP transistor in a TO-92 Plastic Package.

High voltage.

High voltage control circuit.



PIN1 Collector PIN 2 Base PIN 3 Emitter

See Marking Instructions.

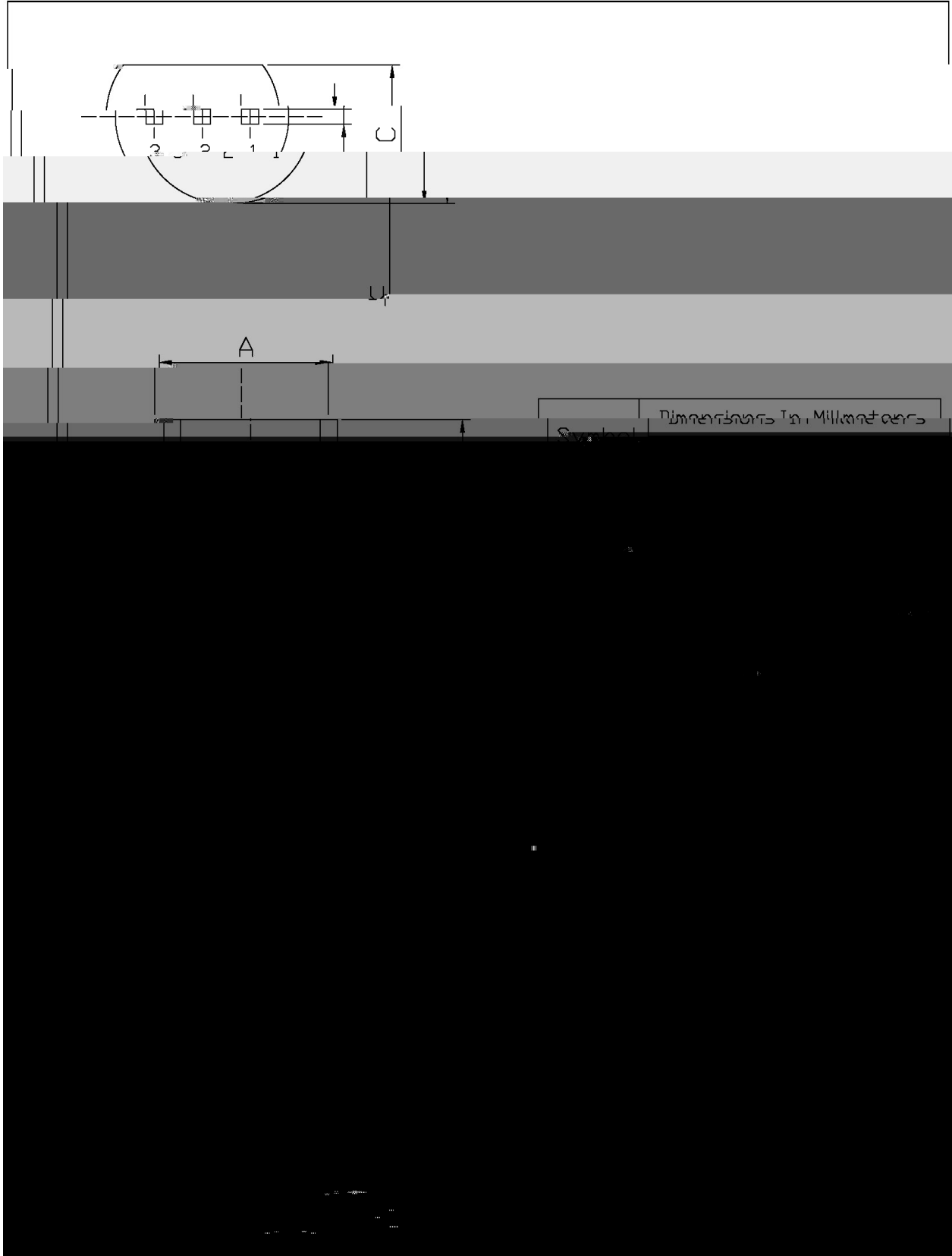
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-400	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-300	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

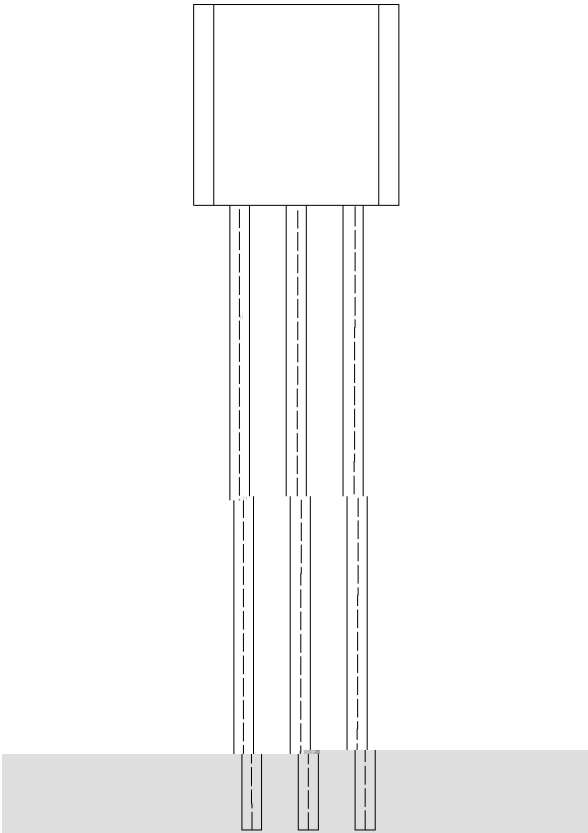
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-400			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -300V$ $I_E = 0$			-0.1	μA
Collector Cut-Off Current	I_{CES}	$V_{CE} = -400V$ $V_{BE} = 0$			-1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -10V$ $I_C = -10mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V$ $I_C = -1.0mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V$ $I_C = -100mA$	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C = -10mA$ $I_B = -1.0mA$			-0.2	V
	$V_{CE(sat)(2)}$	$I_C = -50mA$ $I_B = -5.0mA$			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10mA$ $I_B = -1.0mA$			-0.75	V
Transition Frequency	f_T	$V_{CE} = -5.0V$ $I_C = -10mA$ $f = 30MHz$	50			MHz



T0-92

Unit: mm





BR:



Note:

1 25 150